
2SB1048

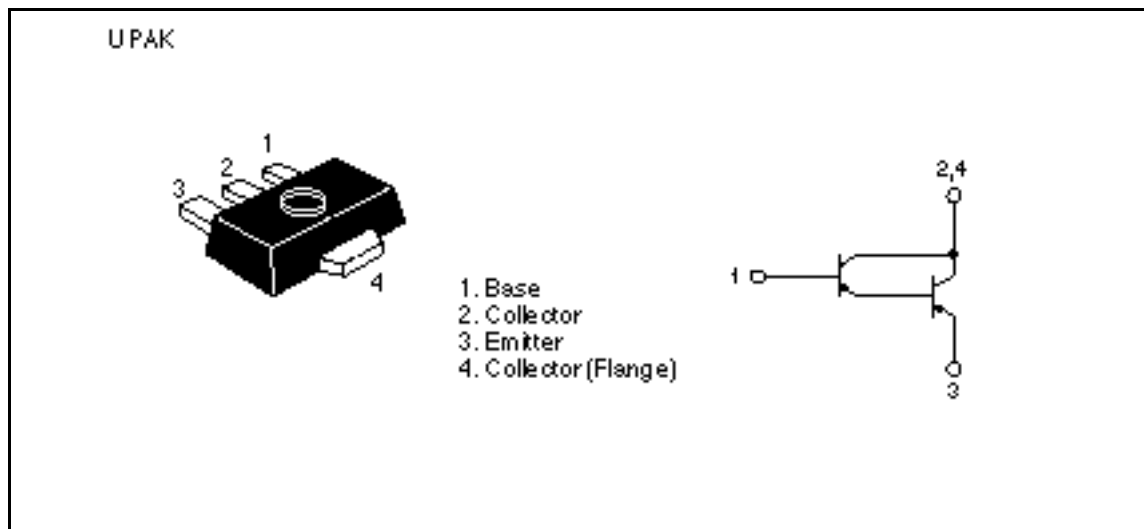
Silicon PNP Epitaxial, Darlington

HITACHI

Application

High gain amplifier

Outline



2SB1048

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-60	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-1	A
Collector peak current	$i_{C(peak)}^{*1}$	-2	A
Collector power dissipation	P_C^{*2}	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. PW 10 ms, Duty cycle 20%

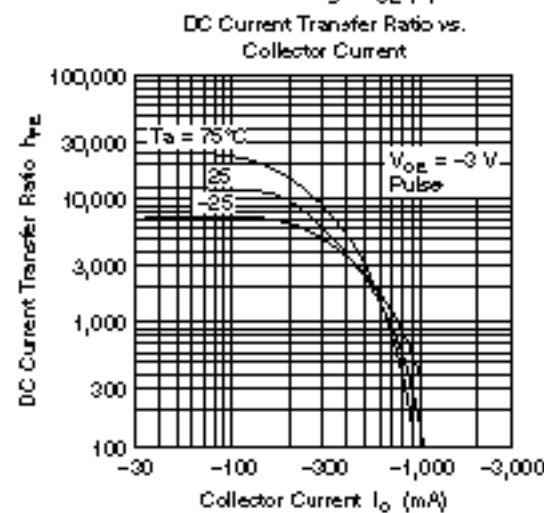
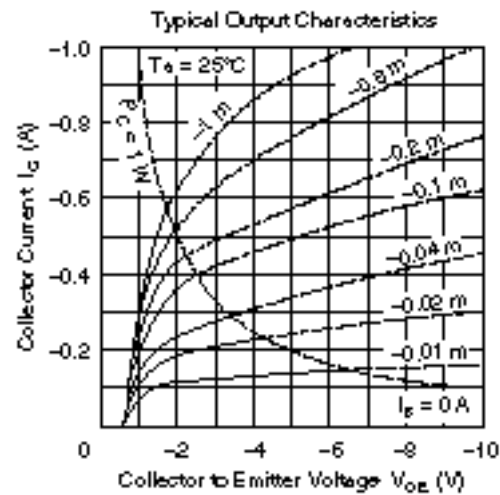
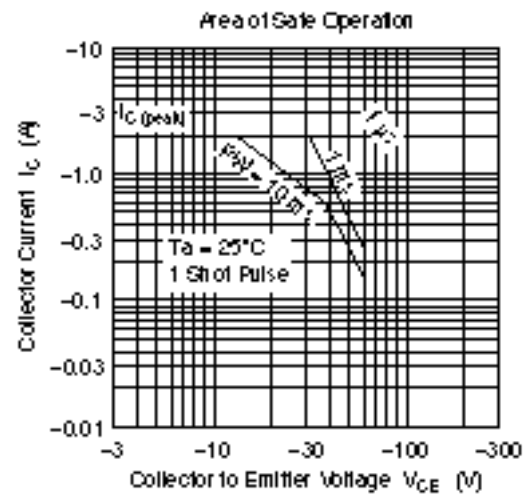
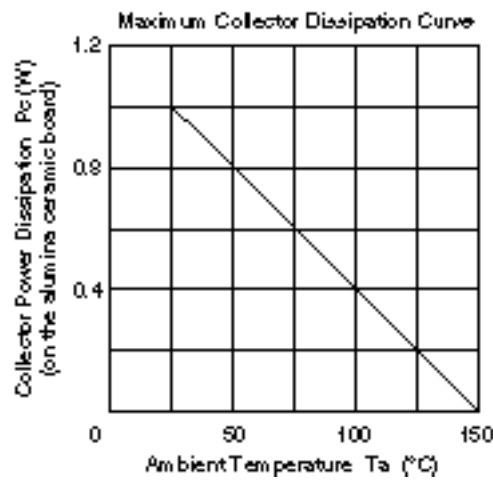
2. Value on the alumina ceramic board (12.5 × 30 × 0.7 mm)

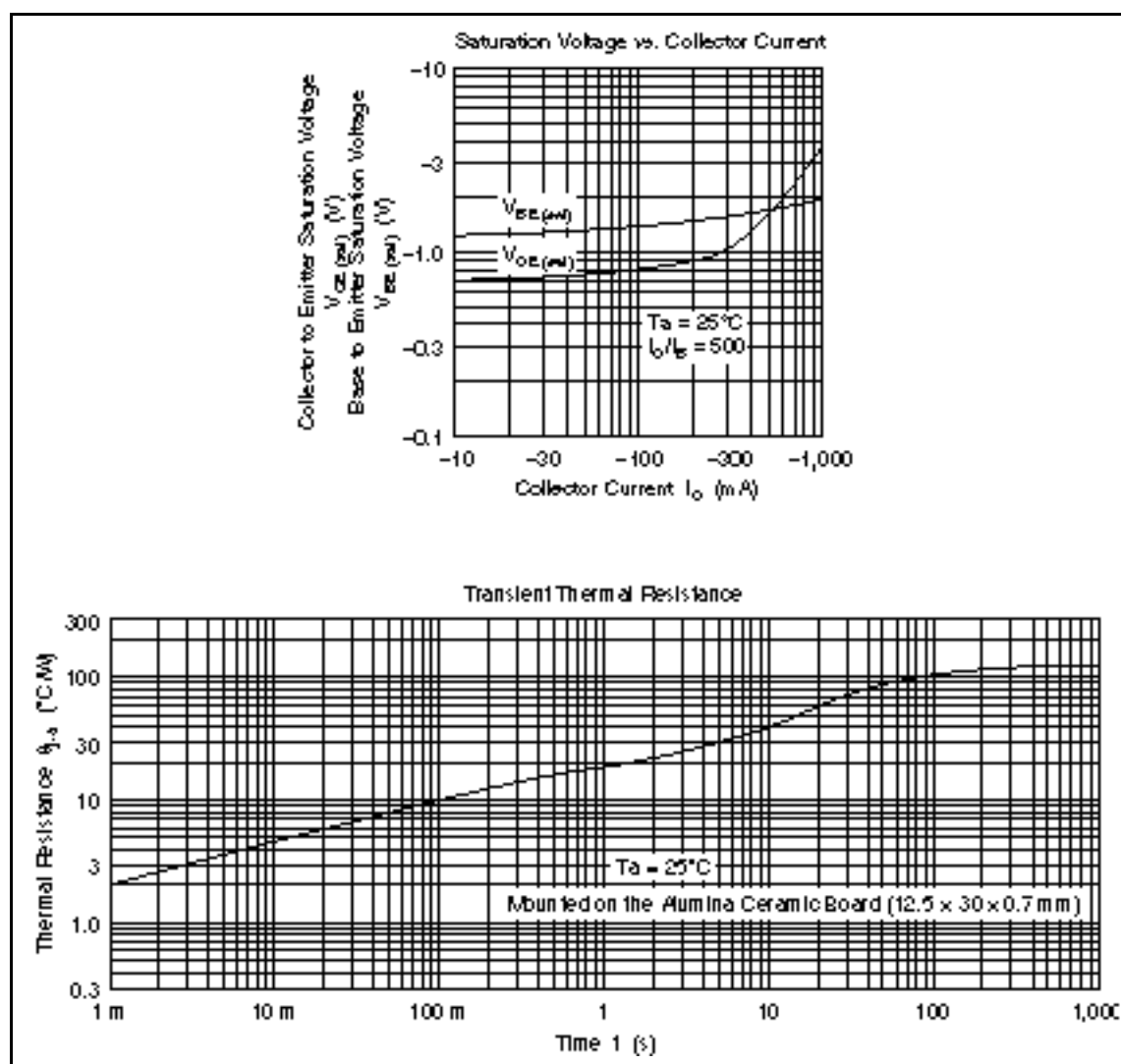
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -1 \text{ mA}, R_{BE} =$
Collector cutoff current	I_{CBO}	—	—	-10	μA	$V_{CB} = -60 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-10	μA	$V_{EB} = -7 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE}	2000	—	100000		$V_{CE} = -3 \text{ V}, I_C = -500 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-2.0	V	$I_C = -500 \text{ mA}, I_B = -1 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-2.0	V	$I_C = -500 \text{ mA}, I_B = -1 \text{ mA}^{*1}$

Notes: 1. Pulse test

2. Marking is "BT"





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